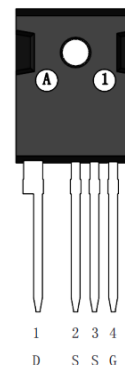


Description

Silicon Carbide (SiC) MOSFET use a completely new technology that provide superior switching performance and higher reliability compared to Silicon. In addition, the low ON resistance and compact chip size ensure low capacitance and gate charge. Consequently, system benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size.

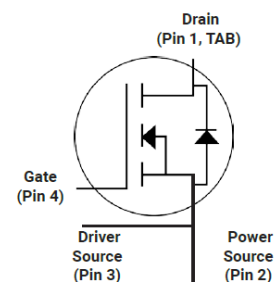
Features

- High Speed Switching with Low Capacitances
- High Blocking Voltage with Low RDS(on)
- Low impedance package with driver source pin
- Easy to parallel and simple to drive
- ROHS Compliant, Halogen free



Application

- EV Charging
- High Voltage DC/DC Converters
- Switch Mode Power Supplies
- Power Factor Correction Modules



Ordering Information

Part Number	Marking	Package	Packaging
ASC20N1200MT4PB	ASC20N1200MT4	TO-247-4	Tube

Absolute Maximum Ratings(Tc=25℃)

Symbol	Parameter	Value	Unit
V _{DS}	Drain-Source Voltage	1200	V
I _D	Drain Current(continuous)at Tc=25℃	20	A
I _D	Drain Current(continuous)at Tc=100℃	12	A
I _{DM}	Drain Current (pulsed)	35	A
V _{GS}	Gate-Source Voltage	-8/+19	V
P _D	Power Dissipation T _C = 25℃	108	W
T _J , Tstg	Junction and Storage Temperature Range	-55 to +175	℃

Electrical Characteristics(T_J = 25℃ unless otherwise specified)
Typical Performance-Static

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV _{DS}	Drain-source Breakdown Voltage	I _D =250uA, V _{GS} =0V	1200			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =1200V, V _{GS} =0V, T _J =25℃			100	uA
I _{GSS}	Gate-body Leakage Current	V _{DS} =0V; V _{GS} =-8 to 19V			250	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D =2mA	1.8	2.5	3.6	V
V _{GS(on)}	Recommended turn-on Voltage	Static		15		V
V _{GS(off)}	Recommended turn-off Voltage			-4		V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} =15V, I _D =10A		160	208	mΩ
		V _{GS} =15V, I _D =10A T _J =175℃		272		mΩ

Typical Performance-Dynamic

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input Capacitance	$V_{DS}=1000V, f=1MHz,$ $V_{AC}=25mV$		715		pF
C_{oss}	Output Capacitance			42		pF
C_{rss}	Reverse Transfer Capacitance			3.2		pF
g_{fs}	Transconductance	$V_{DS}=20V, I_D=10A$		6		S
E_{OSS}	C_{OSS} Stored Energy	$V_{DS}=1000V, f=1MHz$		23		μJ
E_{ON}	Turn-On Energy (Body Diode)	$V_{DS}=800V, V_{GS}=-4/15V,$ $I_D=10A, L=300\mu H$ $T_J=175^\circ C$		105		μJ
E_{OFF}	Turn-Off Energy (Body Diode)			18		μJ
Q_g	Total Gate Charge	$V_{DS}=800V, V_{GS}=-4V/15V,$ $I_D=10A$		26		nC
Q_{gs}	Gate-source Charge			12		nC
Q_{gd}	Gate-Drain Charge			6		nC
$R_{G(int)}$	Internal Gate Resistance	$f=1MHz, V_{AC}=25mV$		5		Ω
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=800V, V_{GS}=-4V/15V,$ $I_D=10A, L=300\mu H$ $R_{ext}=2.5\Omega$		12		ns
t_r	Rise Time			9		ns
$t_{d(off)}$	Turn-off Delay Time			15		ns
t_f	Fall Time			9		ns

Typical Performance-Reverse Diode($T_J = 25^\circ C$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_{FSD}	Forward Voltage	$V_{GS}=0V, I_F=5A, T_J=25^\circ C$		3.5	6	V
		$V_{GS}=0V, I_F=5A, T_J=175^\circ C$		3	6	V
I_S	Continuous Diode Forward Current	$V_{GS}=0V, T_C=25^\circ C$		20		A
t_{rr}	Reverse Recovery Time	$V_{GS}=-4V, I_F=10A,$ $V_R=800V, di/dt=1900$ $A/\mu s, T_J=175^\circ C$		7		nS
Q_{rr}	Reverse Recovery Charge			33		nC
I_{rrm}	Peak Reverse Recovery Current			9		A

Thermal Characteristics

Symbol	Parameter	Value.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.29	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	40	$^\circ C/W$

The values are based on the junction-to case thermal impedance which is measured with the device mounted to a large heat sink assuming maximum junction temperature of $T_J(max)=175^\circ C$

Electrical Characteristics

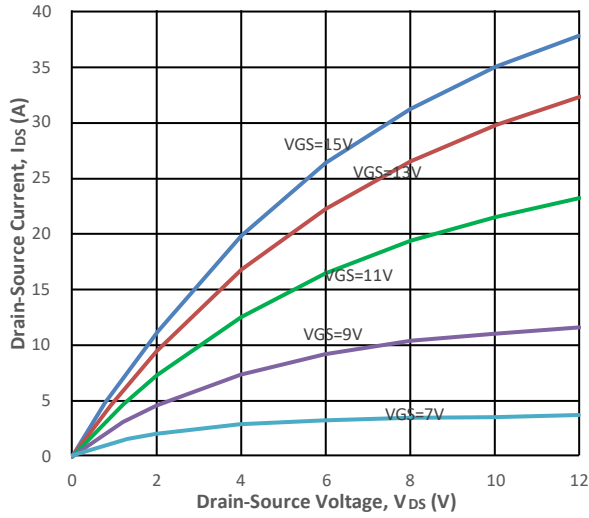
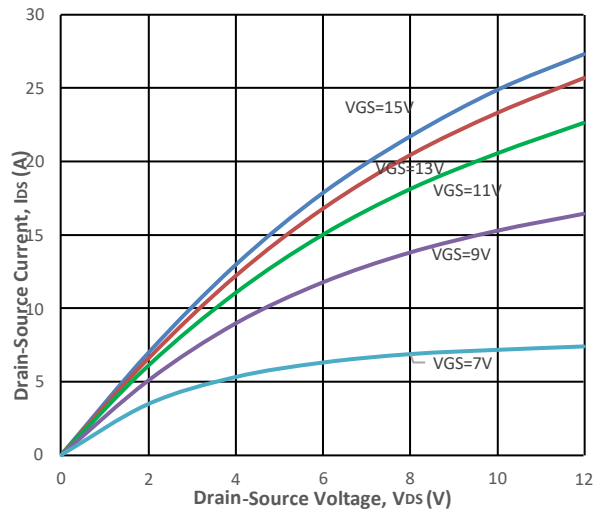
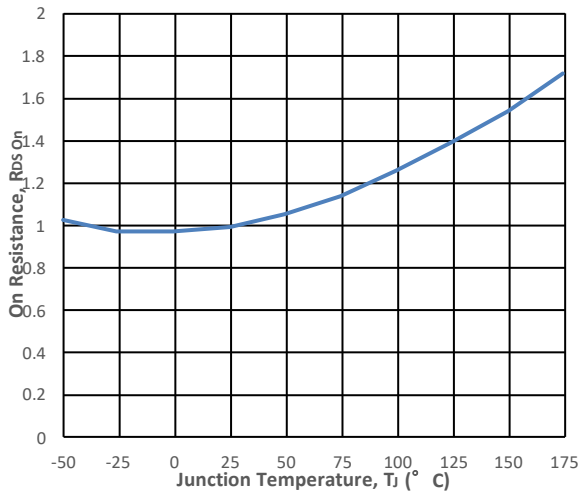
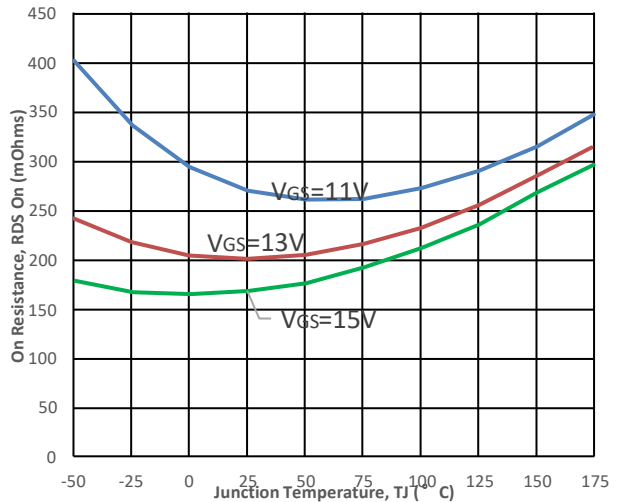
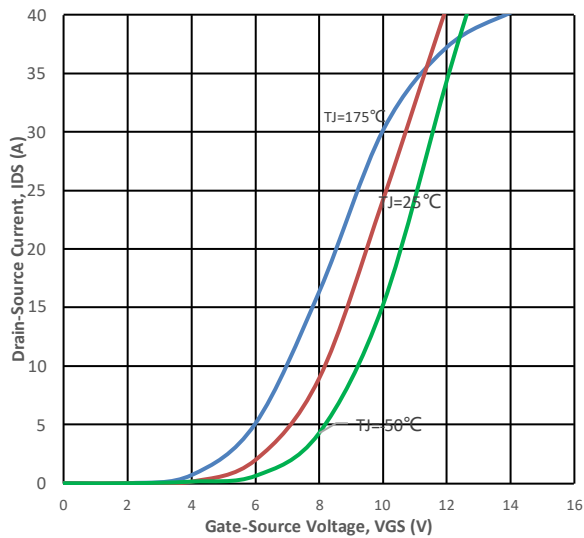
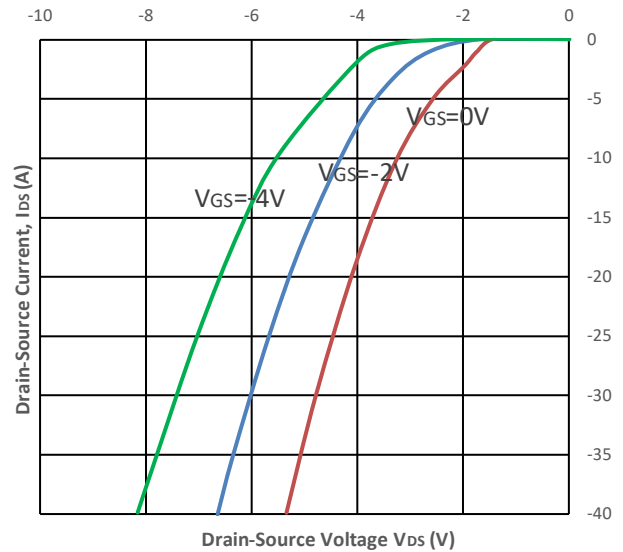
Fig1. Output characteristics ($T_J = 25^\circ\text{C}$)

Fig2. Output characteristics ($T_J = 175^\circ\text{C}$)

Fig3. Normalized On-Resistance vs. Temperature

Fig4. On-Resistance vs. Temperature

Fig5. Transfer Characteristic

Fig6. Body Diode Characteristic at 25°C


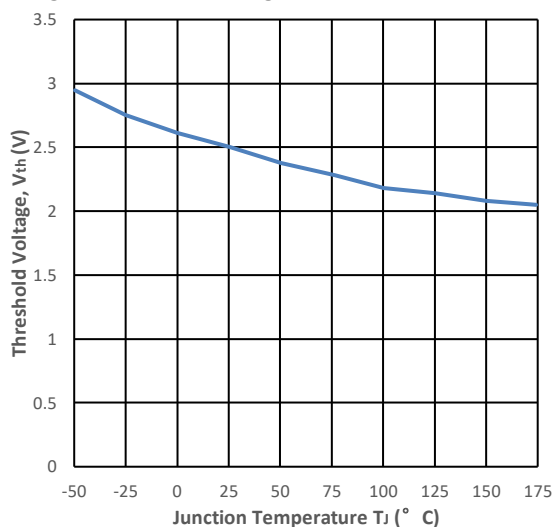
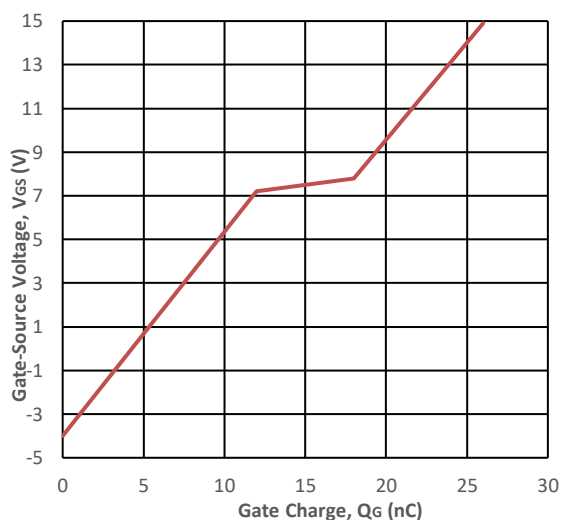
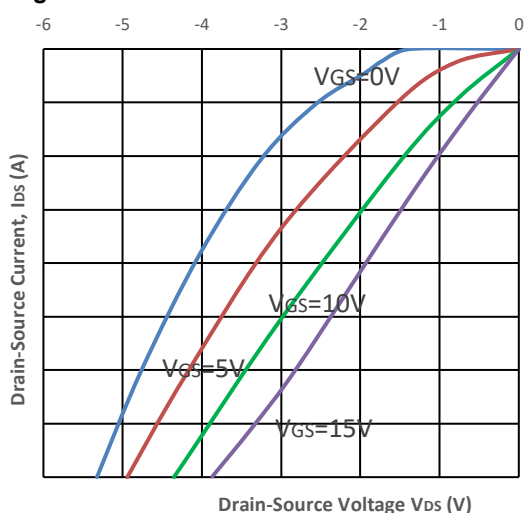
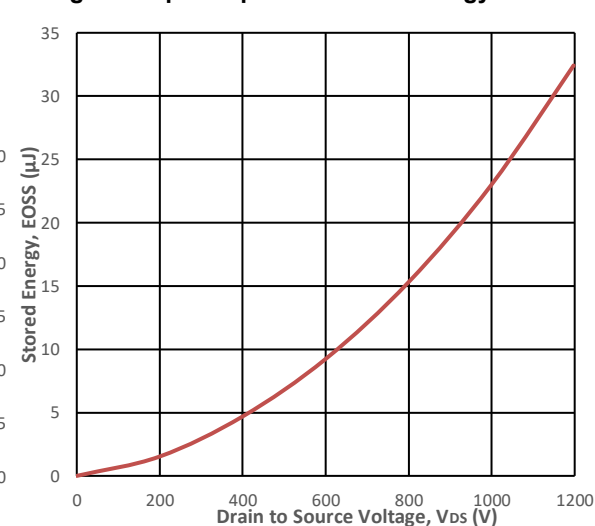
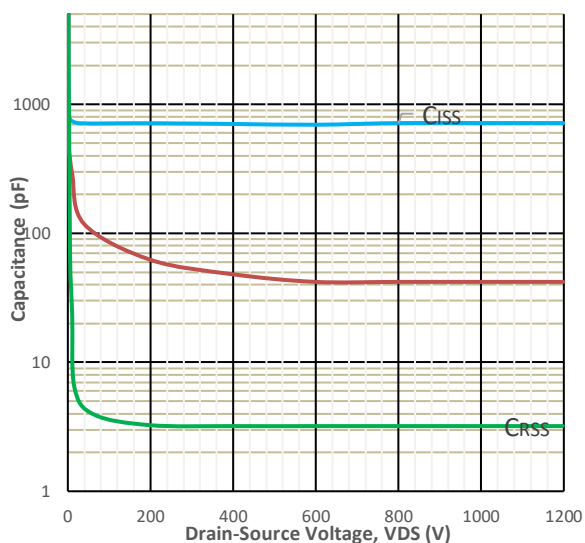
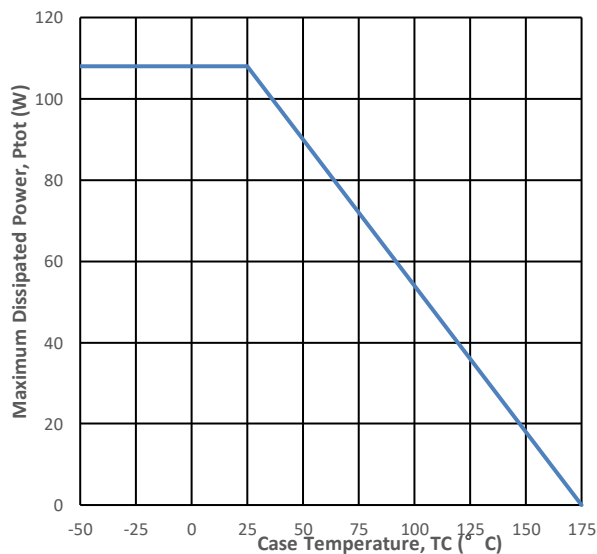
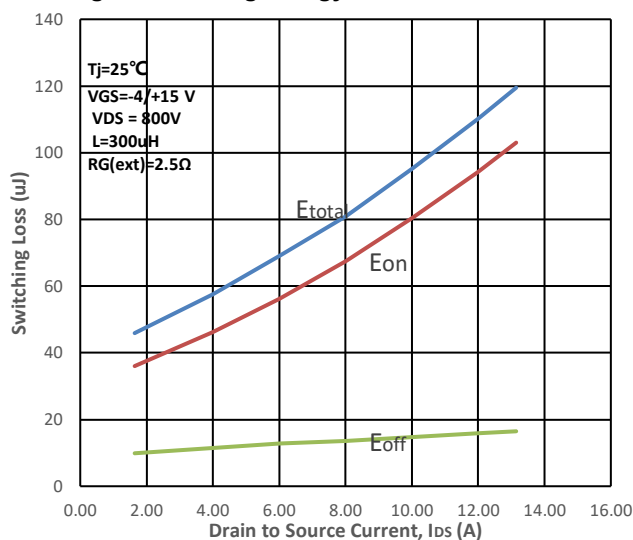
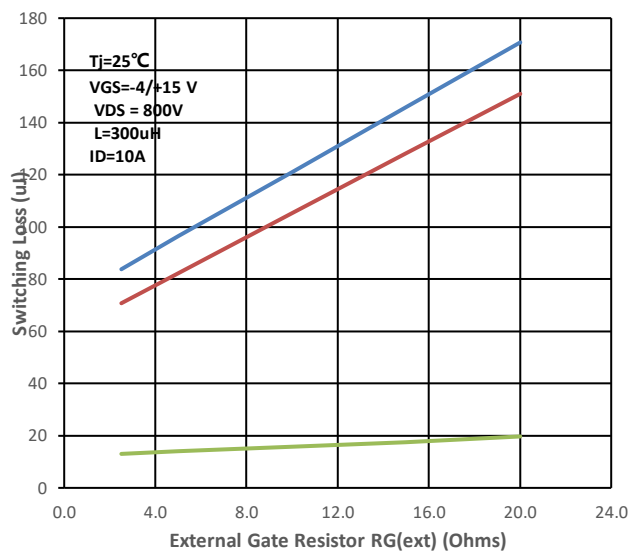
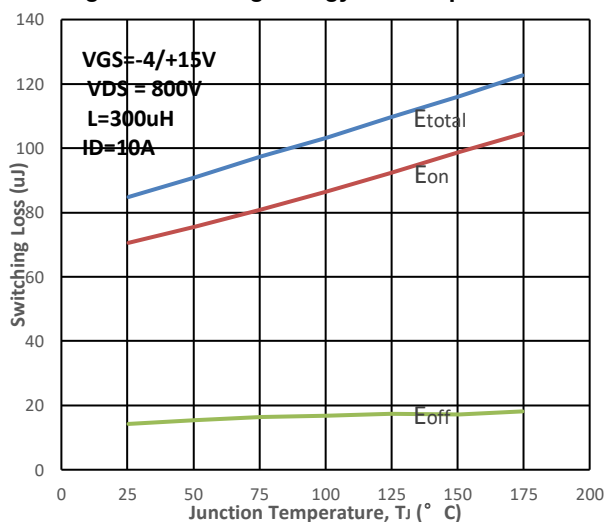
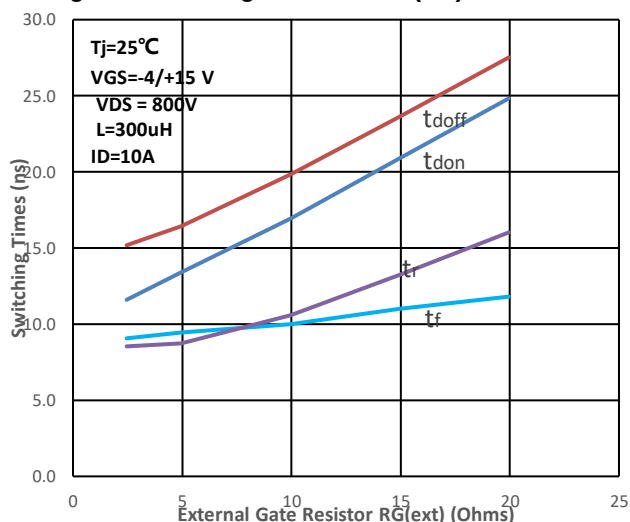
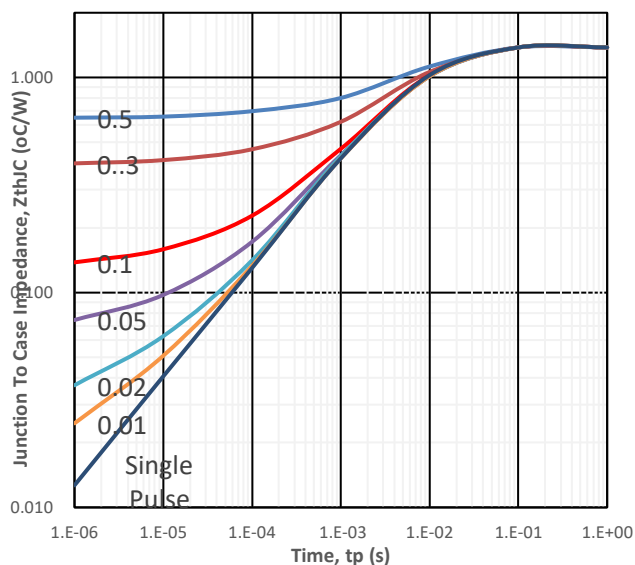
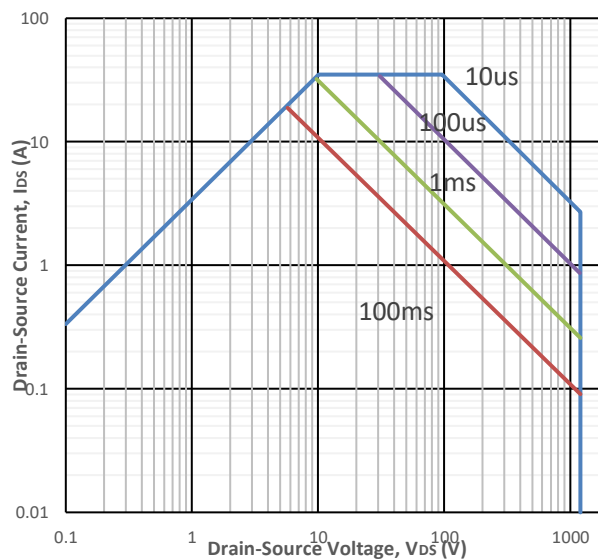
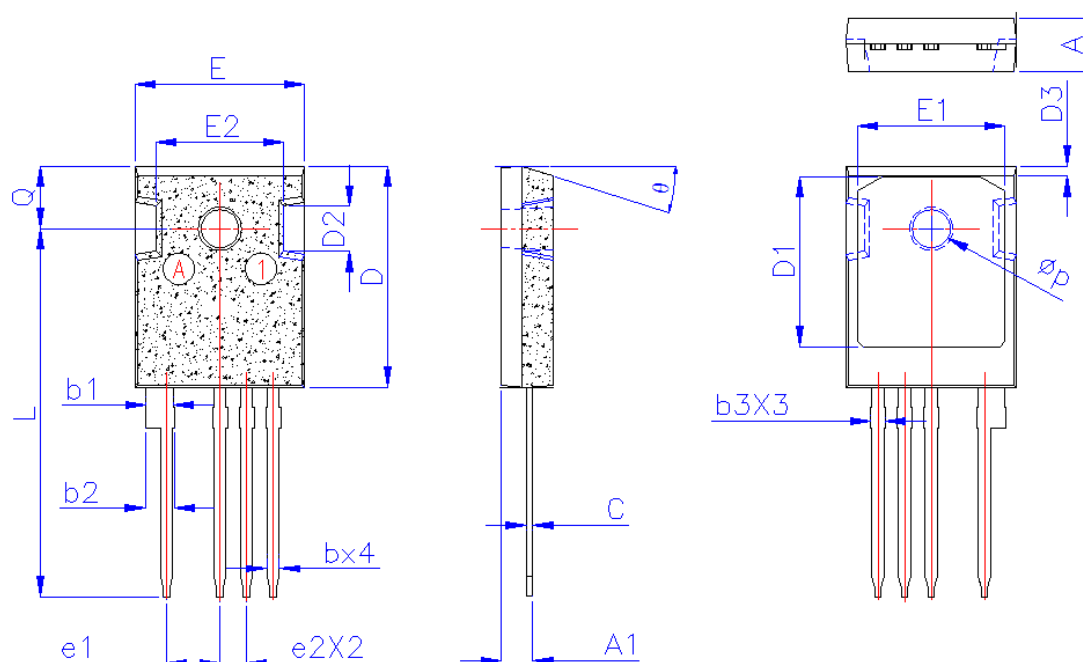
Fig7. Threshold Voltage vs. Temperature

Fig8. Gate Charge Characteristics

Fig9. 3rd Quadrant Characteristic at 25 °C

Fig10. Output Capacitor Stored Energy

Fig11. Capacitances vs. Drain-Source

Fig12. Max Power Dissipation Derating Vs Tc


Fig13. Switching Energy vs. Drain Current

Fig14. Switching Energy vs. RG(ext)

Fig15. Switching Energy vs. Temperature

Fig16. Switching Times vs. RG(ext)

Fig17. Transient Thermal Impedance

Fig18. Safe Operating Area


Package Drawing:

Dimensions (UNIT: mm)

SYMBDLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	TYPE	MAX	MIN	TYPE	MAX
A	4.80	5.00	5.20	0.189	0.197	0.205
A1	2.85	3.00	3.15	0.112	0.118	0.124
b	1.15	1.20	1.25	0.045	0.047	0.049
b1	2.40	2.50	2.60	0.094	0.098	0.102
b2	2.61	2.76	2.91	0.103	0.109	0.115
b3	1.30	1.42	1.57	0.051	0.056	0.062
C	0.55	0.60	0.65	0.022	0.024	0.026
D	20.80	21.00	21.20	0.819	0.827	0.835
D1	15.94	16.24	16.54	0.628	0.639	0.651
D2	4.3 TYPE			0.169 TYPE		
e1	4.93	5.08	5.23	0.194	0.200	0.206
e2	2.39	2.54	2.69	0.094	0.100	0.106
E	15.95	16.15	16.35	0.628	0.636	0.644
E1	13.82	14.02	14.26	0.544	0.552	0.561
E2	12.00	12.20	12.40	0.472	0.480	0.488
L	34.65	35.05	35.45	1.364	1.380	1.396
Q	5.85	5.95	6.05	0.230	0.234	0.238
øP	3.45	3.60	3.75	0.136	0.142	0.148
θ	17.5°			0.689°		

Notes:

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